Rochester Electronics

Datasheet

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceed the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
    - Class Q Military
    - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)

    - Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

74HC132

Quad 2-Input NAND Gate with Schmitt-Trigger Inputs

High−Performance Silicon−Gate CMOS

The 74HC132 is identical in pinout to the LS132. The device inputs are compatible with standard CMOS outputs; with pull−up resistors, they are compatible with LSTTL outputs.

The HC132 can be used to enhance noise immunity or to square up slowly changing waveforms.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements as Defined by JEDEC Standard No. 7A
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- These are Pb−Free Devices

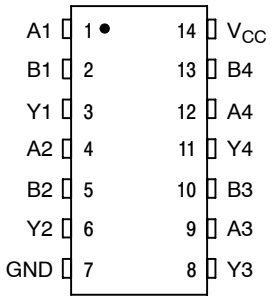


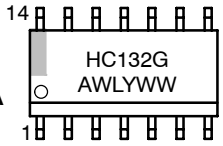
Figure 1. Pin Assignment

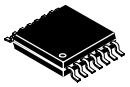
ON Semiconductor®

http://onsemi.com

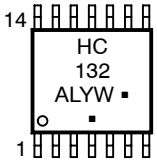
MARKING DIAGRAMS

SOIC−14
D SUFFIX
CASE 751A





TSSOP−14
DT SUFFIX
CASE 948G



HC132 = Device Code
A = Assembly Location
L, WL = Wafer Lot
Y = Year
W, WW = Work Week
G or ▪ = Pb−Free Package
(Note: Microdot may be in either location)

FUNCTION TABLE

Inputs		Output
A	**B**	**Y**
L	L	H
L	H	H
H	L	H
H	H	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

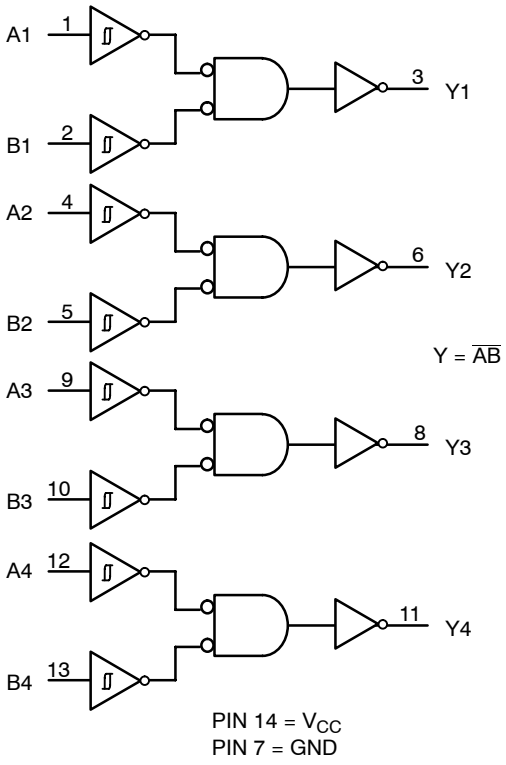


Figure 2. Logic Diagram

ORDERING INFORMATION

Device	Package	Shipping†
74HC132DR2G	SOIC−14 (Pb−Free)	2500 / Tape & Reel
74HC132DTR2G	TSSOP−14*	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb−Free.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{CC}	Positive DC Supply Voltage		−0.5 to +7.0	V
V_{IN}	Digital Input Voltage		−0.5 to +7.0	V
V_{OUT}	DC Output Voltage	Output in 3−State High or Low State	−0.5 to +7.0 −0.5 to V_{CC} +0.5	V
I_{IK}	Input Diode Current		−20	mA
I_{OK}	Output Diode Current		±20	mA
I_{OUT}	DC Output Current, per Pin		±25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins		±75	mA
I_{GND}	DC Ground Current per Ground Pin		±75	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance	14−SOIC 14−TSSOP	125 170	°C/W
P_D	Power Dissipation in Still Air at 85°C	SOIC TSSOP	500 450	mW
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 30% − 35%	UL 94 V−0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2)	>2000 >200	V
$I_{Latchup}$	Latchup Performance	Above V_{CC} and Below GND at 85°C (Note 3)	±300	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Tested to EIA/JESD22−A114−A.
2. Tested to EIA/JESD22−A115−A.
3. Tested to EIA/JESD78.
4. For high frequency or heavy load considerations, see Chapter 2the ON Semiconductor High−Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V_{IN}, V_{OUT}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	−55	+125	°C
t_r, t_f	Input Rise and Fall Time (Figure 3)	−	No Limit (Note 5)	ns

5. When $V_{IN} \sim 0.5\ V_{CC}$, I_{CC} >> quiescent current.
6. Unused inputs may not be left open. All inputs must be tied to a high−logic voltage level or a low−logic input voltage level.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} (V)	Guaranteed Limit			Unit
				−55°C to 25°C	≤85°C	≤125°C	
V_{T+}max	Maximum Positive−Going Input Threshold Voltage (Figure 5)	V_{OUT} = 0.1 V $\|I_{OUT}\| \le 20$ μA	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
V_{T+}min	Minimum Positive−Going Input Threshold Voltage (Figure 5)	V_{OUT} = 0.1 V $\|I_{OUT}\| \le 20$ μA	2.0 4.5 6.0	1.0 2.3 3.0	0.95 2.25 2.95	0.95 2.25 2.95	V
V_{T-}max	Maximum Negative−Going Input Threshold Voltage (Figure 5)	$V_{OUT} = V_{CC} - 0.1$ V $\|I_{OUT}\| \le 20$ μA	2.0 4.5 6.0	0.9 2.0 2.6	0.95 2.05 2.65	0.95 2.05 2.65	V
V_{T-}min	Minimum Negative−Going Input Threshold Voltage (Figure 5)	$V_{OUT} = V_{CC} - 0.1$ V $\|I_{OUT}\| \le 20$ μA	2.0 4.5 6.0	0.3 0.9 1.2	0.3 0.9 1.2	0.3 0.9 1.2	V
$V_H$max (Note 7)	Maximum Hysteresis Voltage (Figure 5)	V_{OUT} = 0.1 V or V_{CC} − 0.1 V $\|I_{OUT}\| \le 20$ μA	2.0 4.5 6.0	1.2 2.25 3.0	1.2 2.25 3.0	1.2 2.25 3.0	V
$V_H$min (Note 7)	Minimum Hysteresis Voltage (Figure 5)	V_{OUT} = 0.1 V or V_{CC} − 0.1 V $\|I_{OUT}\| \le 20$ μA	2.0 4.5 6.0	0.2 0.4 0.5	0.2 0.4 0.5	0.2 0.4 0.5	V
V_{OH}	Minimum High−Level Output Voltage	$V_{IN} \le$ V_{T-}min or V_{T+}max $\|I_{OUT}\| \le 20$ μA	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{IN} \le$ −V_{T-}min or V_{T+}max $\|I_{OUT}\| \le 4.0$ mA $\|I_{OUT}\| \le 5.2$ mA	 4.5 6.0	 3.98 5.48	 3.84 5.34	 3.7 5.2	
V_{OL}	Maximum Low−Level Output Voltage	$V_{IN} \ge$ V_{T+}max $\|I_{OUT}\| \le 20$ μA	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{IN} \ge$ V_{T+}max $\|I_{OUT}\| \le 4.0$ mA $\|I_{OUT}\| \le 5.2$ mA	4.5 6.0	0.26 0.26	0.33 0.33	0.4 0.4	
I_{IN}	Maximum Input Leakage Current	$V_{IN} = V_{CC}$ or GND	6.0	±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	$V_{IN} = V_{CC}$ or GND I_{OUT} = 0 μA	6.0	2.0	20	40	μA

7. $V_H$min > (V_{T+}min) − (V_{T-}max); $V_H$max = (V_{T+}max) + (V_{T-}min).
8. Information on typical parametric values can be found in the ON Semiconductor High−Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input $t_r = t_f$ = 6.0 ns)

Symbol	Parameter	V_{CC} (V)	Guaranteed Limit			Unit
			−55°C to 25°C	≤85°C	≤125°C	
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Input A or B to Output Y (Figures 3 and 4)	2.0 4.5 6.0	125 25 21	155 31 26	190 38 32	ns
t_{TLH}, t_{THL}	Maximum Output Transition Time, Any Output (Figures 3 and 4)	2.0 4.5 6.0	75 15 13	95 19 16	110 22 19	ns
C_{in}	Maximum Input Capacitance	—	10	10	10	pF

9. For propagation delays with loads other than 50 pF, and information on typical parametric values, see the ON Semiconductor High−Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V_{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (per Gate) (Note 10)	24	pF

10. Used to determine the no−load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see the ON Semiconductor High−Speed CMOS Data Book (DL129/D).

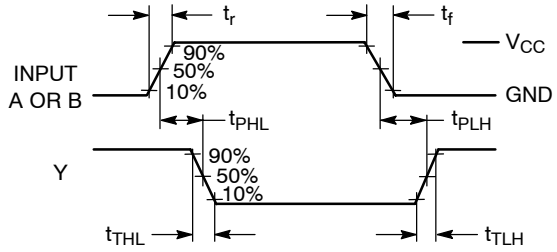
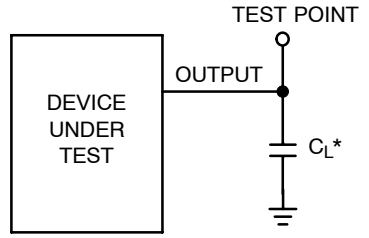


Figure 3. Switching Waveforms



*Includes all probe and jig capacitance

Figure 4. Test Circuit

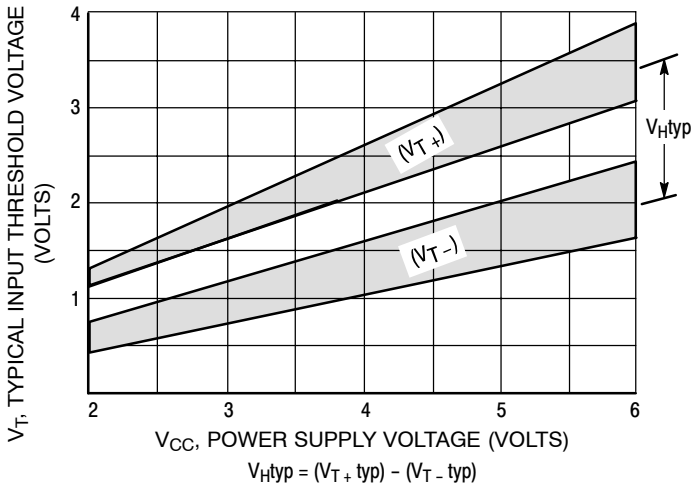


Figure 5. Typical Input Threshold, V_{T+}, V_{T-} Versus Power Supply Voltage

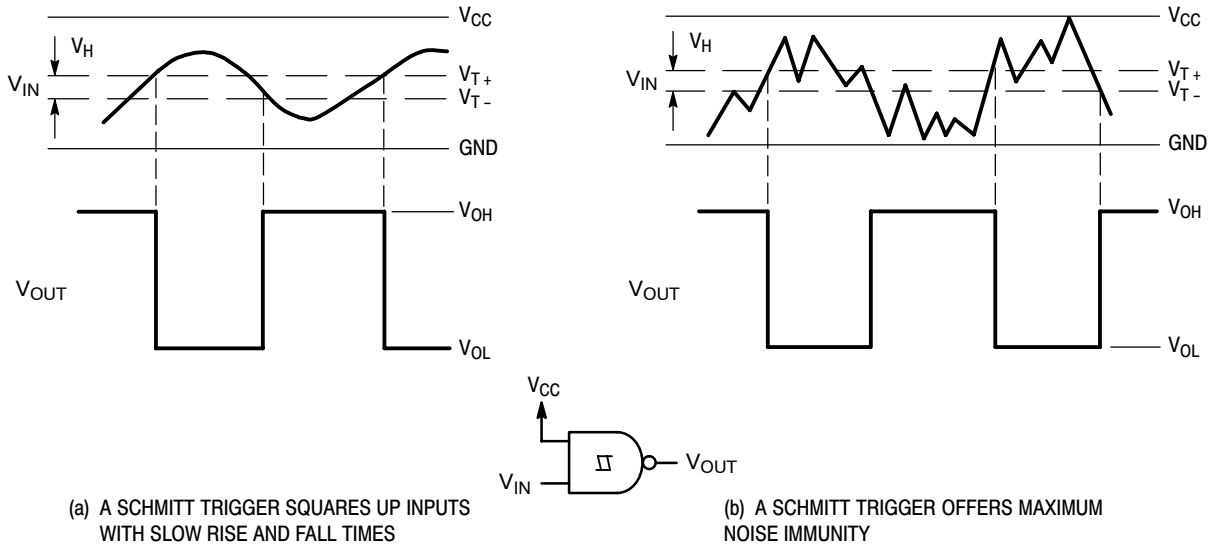
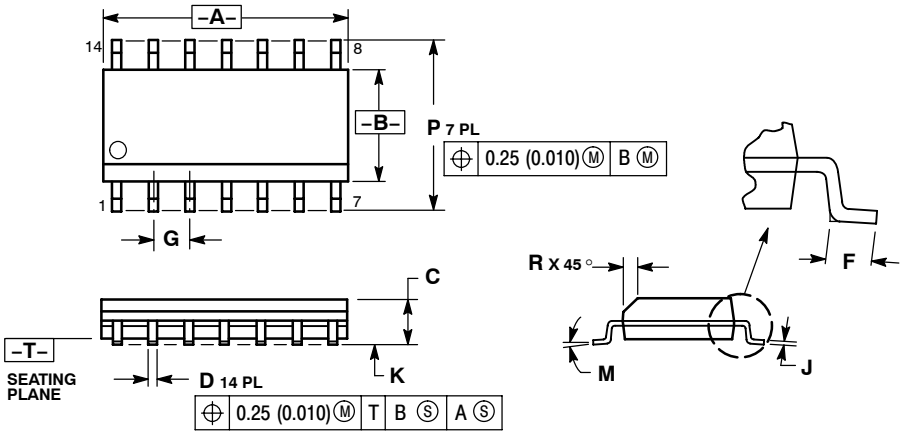


Figure 6. Typical Schmitt−Trigger Applications

PACKAGE DIMENSIONS

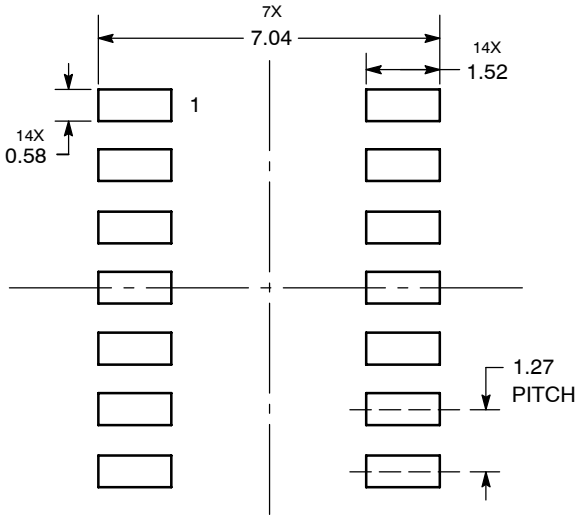
SOIC−14
CASE 751A−03
ISSUE H



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7 °	0 °	7 °
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

SOLDERING FOOTPRINT*

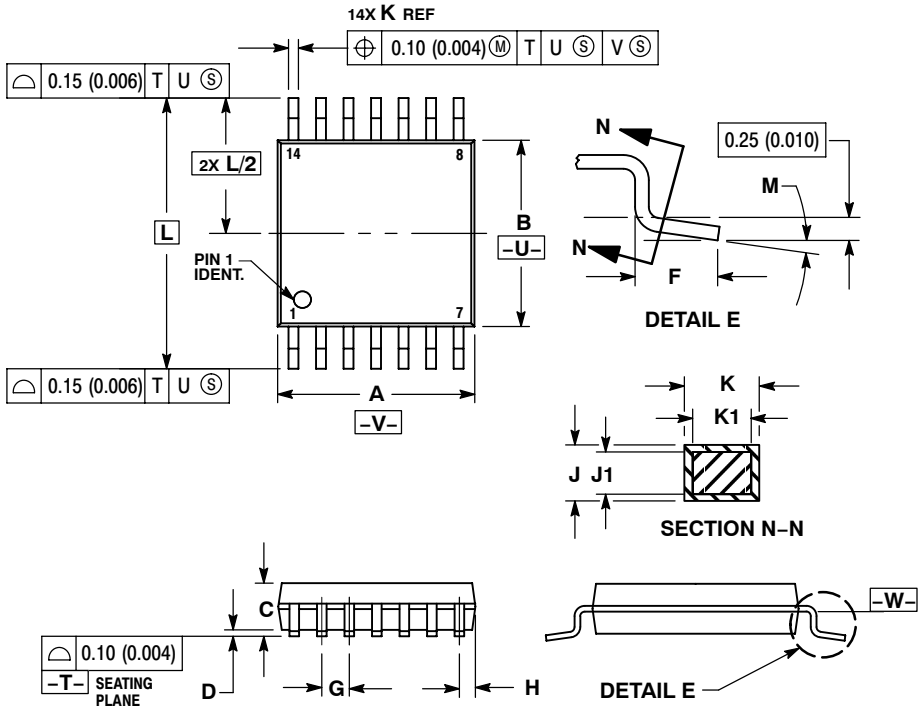


DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

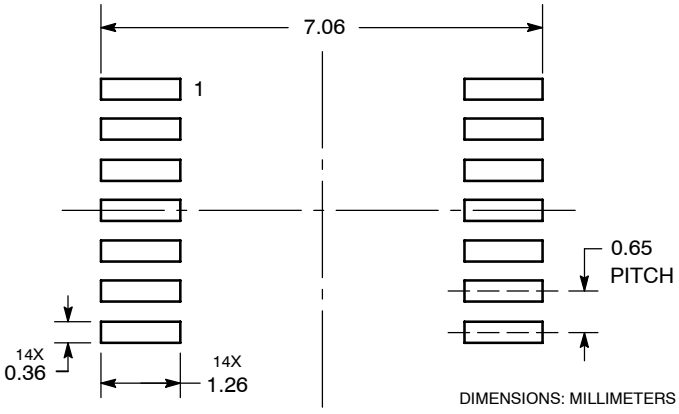
TSSOP−14
CASE 948G−01
ISSUE B



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	−−−	1.20	−−−	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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